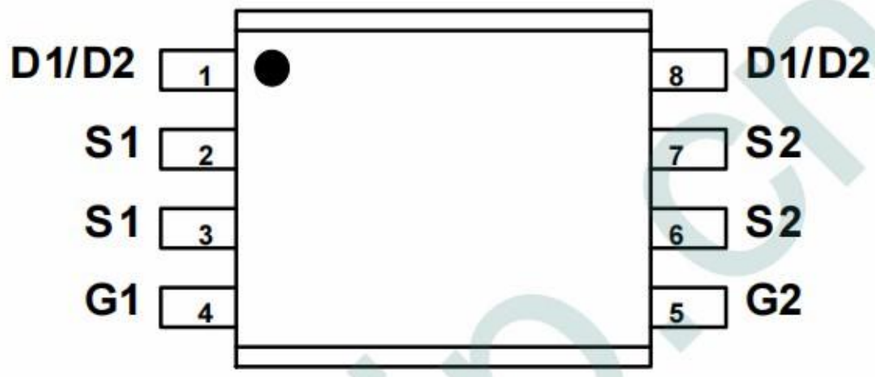
8205HA/W

20V N-Channel Enhancement Mode MOSFET

RDS(ON), Vgs@2.5V, Ids@4.0A = 23mΩ
RDS(ON), Vgs@4.5V, Ids@4.0A = 19mΩ

Features

- High Power and current handing capability
- Lead free product is acquired
- Surface Mount Package



TSSOP-8

Absolute Max Ratings at Ta=25℃ (Note1)

Parameter	Symbol	Maximum	Units
Drain to Source Voltage	VDSS	20	V
Gate to Source Voltage	VGSS	±12	V
Drain Current-Continuous	ID	6	A
Drain Current (Pulse)	IDM	20	A
Maximum Power Dissipation	PD	1.96	W
Operating Junction and Storage Temperature Range	Tj，Tstg	-55 to +150	℃
Lead Temperature for Soldering Purposes (1/8″ from case for 10 s)	TL	260	℃

Note 1: Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

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